60V N-Channel MOSFET

Lead Free Package and Finish

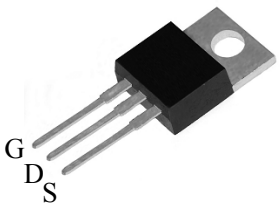
BV_{DSS}	$R_{DS(ON),typ.}$	I_D[2]
60V	6.1mΩ	105A

General Features

- Proprietary New Trench Technology
- $R_{DS(ON),typ.}$=6.1 mΩ@V_{GS}=10V
- Low Gate Charge Minimize Switching Loss
- Fast Recovery Body Diode

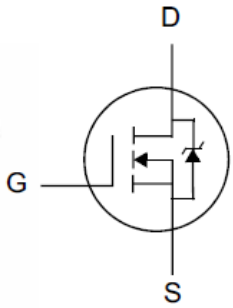
Applications

- High efficiency DC/DC Converters
- Synchronous Rectification
- UPS Inverter



TO-220

Package No to Scale



Ordering Information

Part Number	Package	Brand
PTP08N06NB	TO-220	

Absolute Maximum Ratings

T_C=25℃ unless otherwise specified

Symbol	Parameter	PTP08N06NB	Unit
V_{DSS}	Drain-to-Source Voltage[1]	60	V
V_{GSS}	Gate-to-Source Voltage	±20	
I_D	Continuous Drain Current $^{TC = 25°C}$	105	A
	Continuous Drain Current $^{TC = 100°C}$	73.5	
I_{DM}	Pulsed Drain Current at V_{GS}=10V[2,4]	420	
IAs	Avalanche Current	30	
E_{AS}	Single Pulse Avalanche Energy	450	mJ
dv/dt	Peak Diode Recovery dv/dt[3]	5.0	V/ns
P_D	Power Dissipation	187.5	W
	Derating Factor above 25℃	1.25	W/℃
T_L T_{PAK}	Maximum Temperature for Soldering Leads at 0.063in (1.6mm) from Case for 10 seconds, Package Body for 10 seconds	300 260	℃
T_J& T_{STG}	Operating and Storage Temperature Range	-55 to 175	

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.

Thermal Characteristics

Symbol	Parameter	PTP08N06A	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.8	℃/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62	

Electrical Characteristics

OFF Characteristics

T_J =25℃ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	60	--	--	V	V_{GS}=0V, I_D=250uA
I_{DSS}	Drain-to-Source Leakage Current	--	--	1	uA	V_{DS}=60V, V_{GS}=0V
		--	--	100		V_{DS}=48V, V_{GS}=0V, T_J =125℃
I_{GSS}	Gate-to-Source Leakage Current	--	--	+100	nA	V_{GS}=+20V, V_{DS}=0V
		--	--	-100		V_{GS}=-20V, V_{DS}=0V

ON Characteristics

T_J =25℃ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	--	6.1	7.5	mΩ	V_{GS}=10V, I_D=50A [5]
$V_{GS(TH)}$	Gate Threshold Voltage	2.0	--	4.0	V	V_{DS}=V_{GS}, I_D=250uA
gfs	Forward Transconductance	--	50	--	S	V_{DS}=10V,I_D=25A [5]

Dynamic Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
C_{iss}	Input Capacitance	--	3800	--	pF	V_{GS}=0V, V_{DS}=25V, f=1.0MH_Z
C_{rss}	Reverse Transfer Capacitance	--	380	--		
C_{oss}	Output Capacitance	--	298	--		
Q_g	Total Gate Charge	--	70	--	nC	V_{DD}=30V, I_D=55A, V_{GS}=0 to 10V
Q_{gs}	Gate-to-Source Charge	--	25	--		
Q_{gd}	Gate-to-Drain (Miller) Charge	--	14	--		

Resistive Switching Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$t_{d(ON)}$	Turn-on Delay Time	--	25	--	nS	V_{DD}=30V, I_D=55A, V_{GS}= 10V R_G=2.5Ω
t_{rise}	Rise Time	--	12	--		
$t_{d(OFF)}$	Turn-Off Delay Time	--	38	--		
t_{fall}	Fall Time	--	10	--		

Source-Drain Body Diode Characteristics

T_J=25℃ unless otherwise specified

Symbol	Parameter	Min	Typ.	Max.	Unit	Test Conditions
I_{SD}	Continuous Source Current[2]	--	--	105	A	Integral PN-diode in MOSFET
I_{SM}	Pulsed Source Current[2]	--	--	420		
V_{SD}	Diode Forward Voltage	--	--	1.2	V	I_S=30A, V_{GS}=0V
trr	Reverse recovery time	--	45	--	ns	V_{GS}=0V ,I_F=30A, di_F/dt=100A/μs
Qrr	Reverse recovery charge	--	55	--	nC	

Note:

[1] T_J=+25℃ to +175℃
[2] Silicon limited current only.
[3].Package limited current
[4] Repetitive rating; pulse width limited by maximum junction temperature.
[5] Pulse width≤380μs; duty cycle≤2%.

Typical Characteristics

Figure 1. Output Characteristics

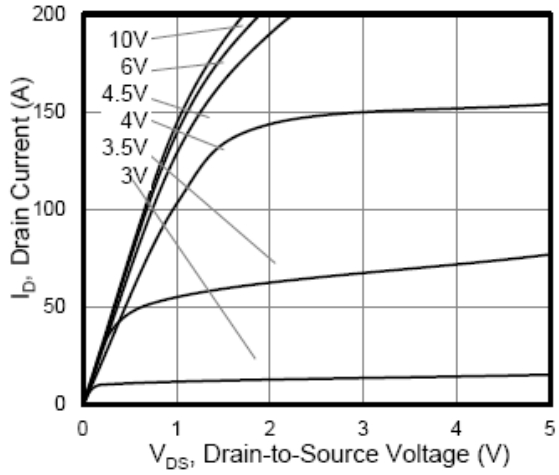


Figure 2. Transfer Characteristics

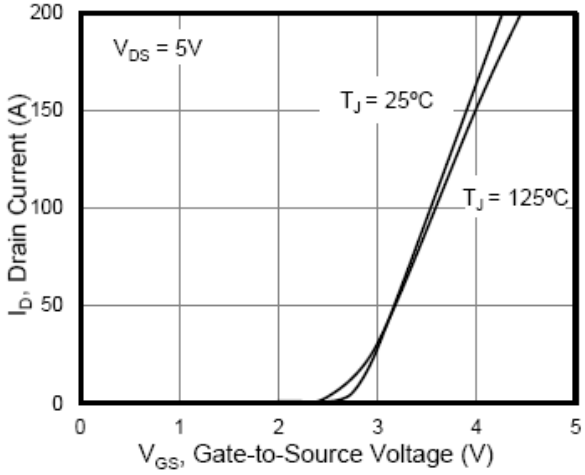


Figure 3. On-Resistance vs. Drain Current

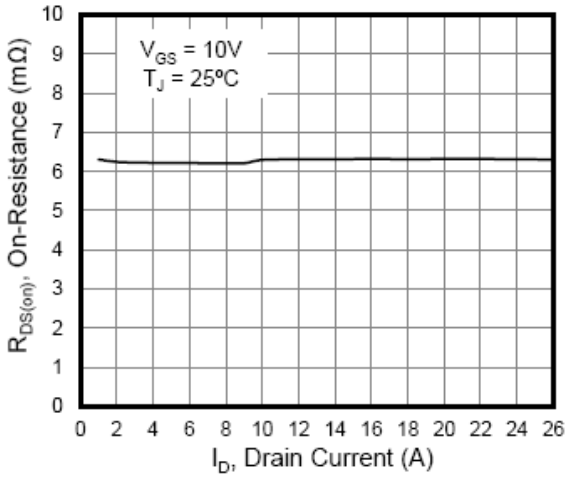


Figure 4. Capacitance

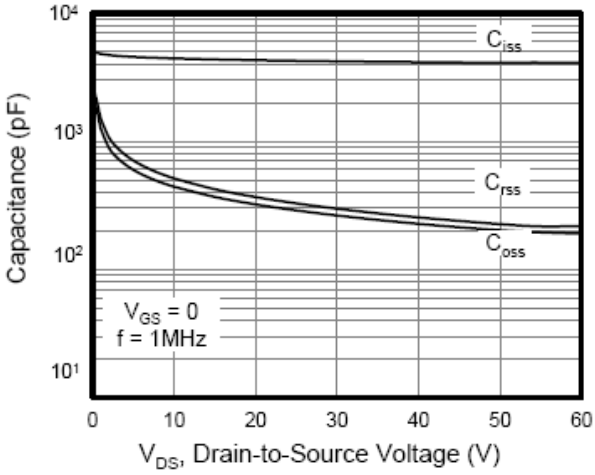


Figure 5. Gate Charge

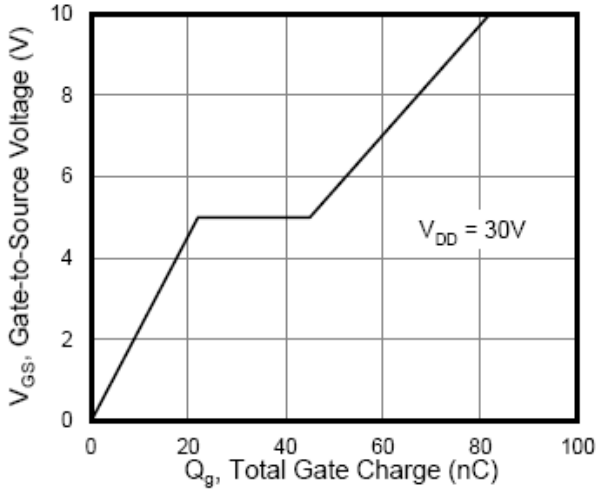
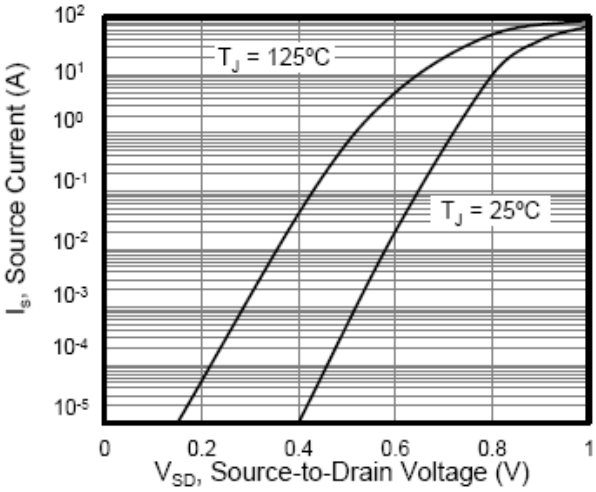


Figure 6. Body Diode Forward Voltage



Typical Characteristics(Cont.)

Figure 7. On-Resistance vs. Junction Temperature

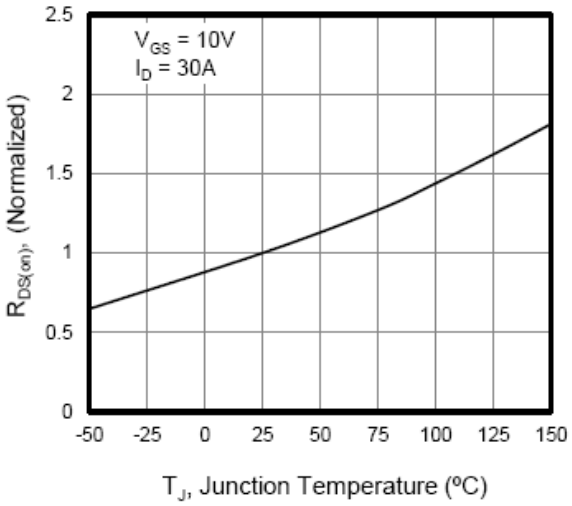


Figure 8. Threshold Voltage vs. Junction Temperature

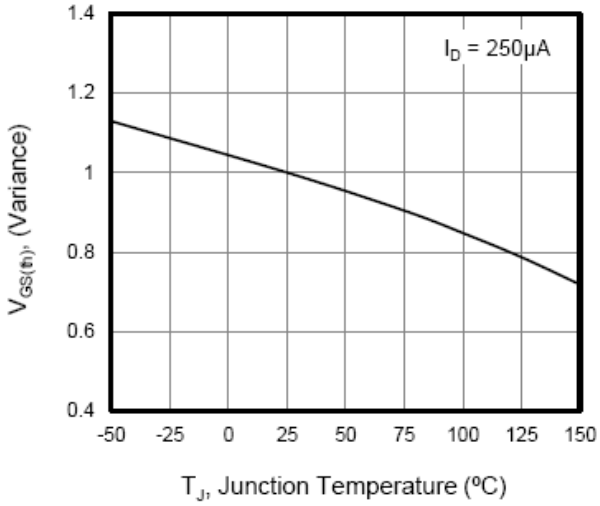


Figure 9. Transient Thermal Impedance

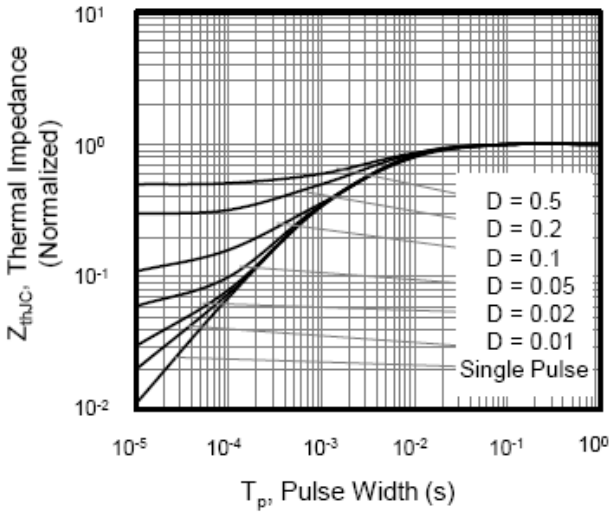
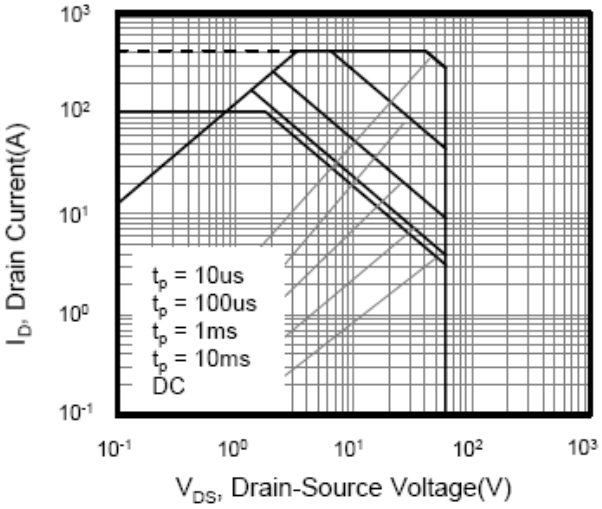


Figure 10. Safe operation area



Test Circuits and Waveforms

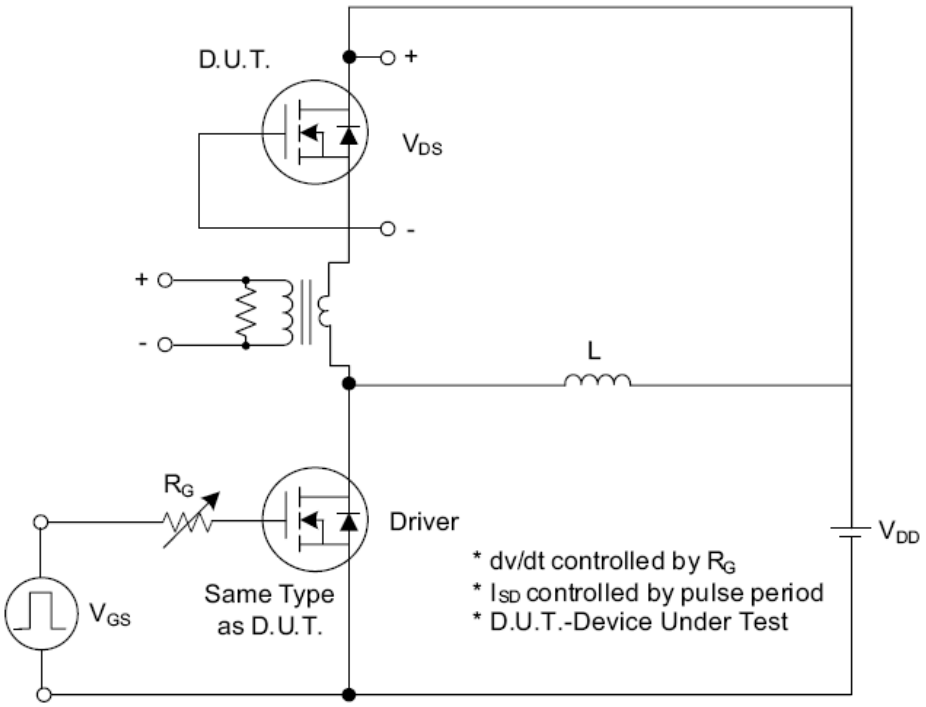


Fig. 1.1 Peak Diode Recovery dv/dt Test Circuit

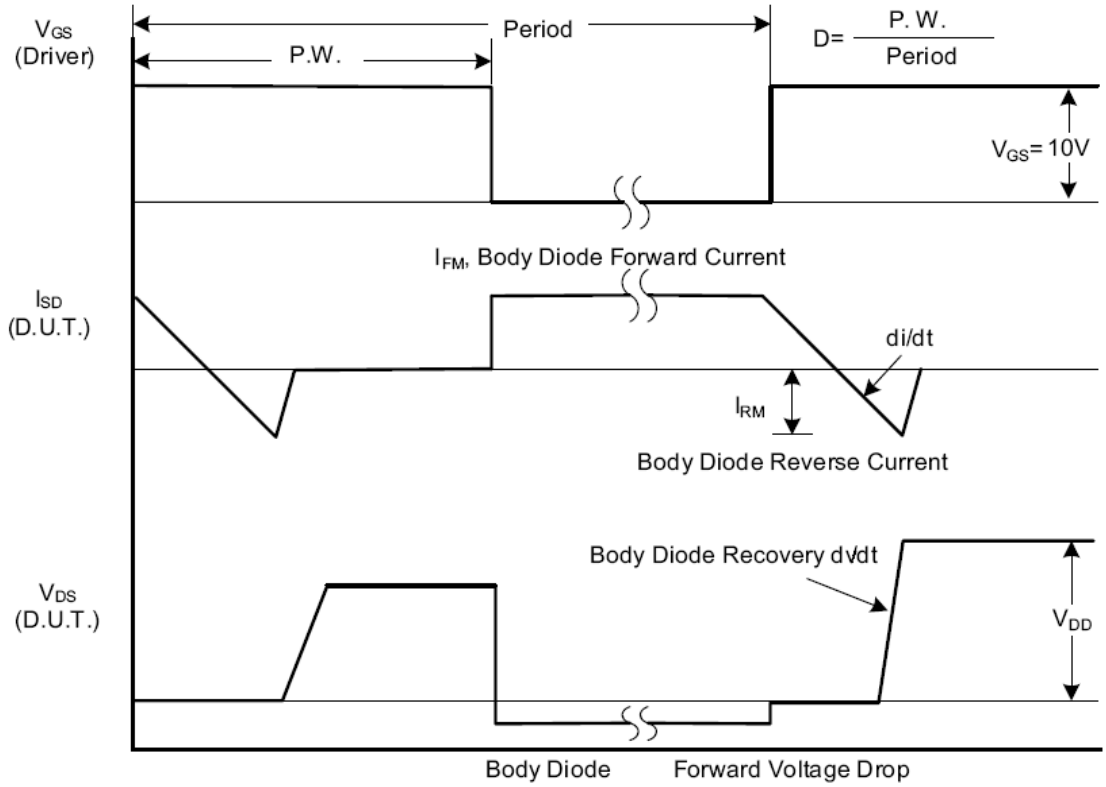


Fig. 1.2 Peak Diode Recovery dv/dt Waveforms

Test Circuits and Waveforms (Cont.)

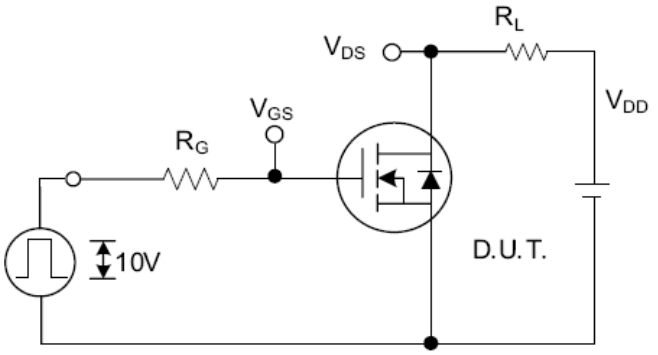


Fig. 2.1 Switching Test Circuit

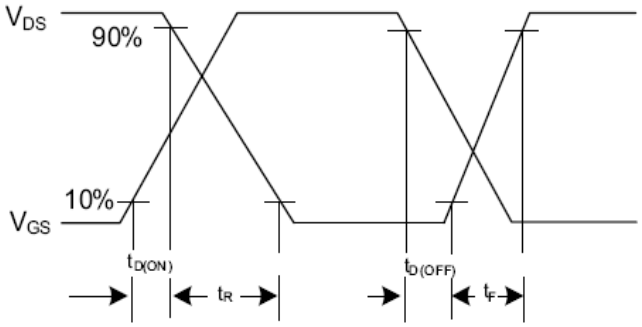


Fig. 2.2 Switching Waveforms

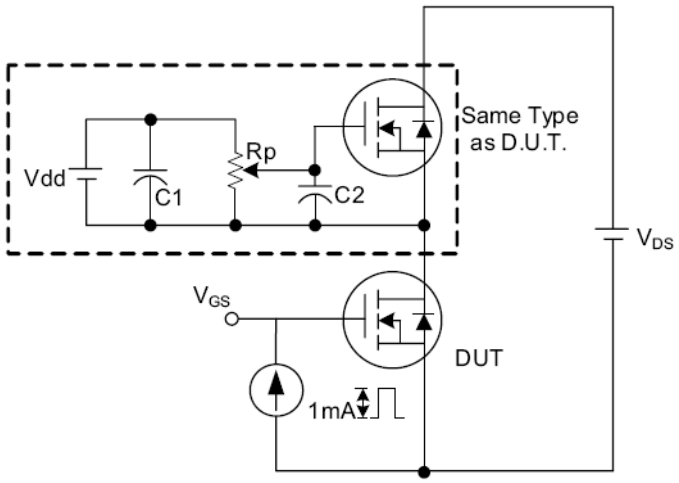


Fig. 3 . 1 Gate Charge Test Circuit

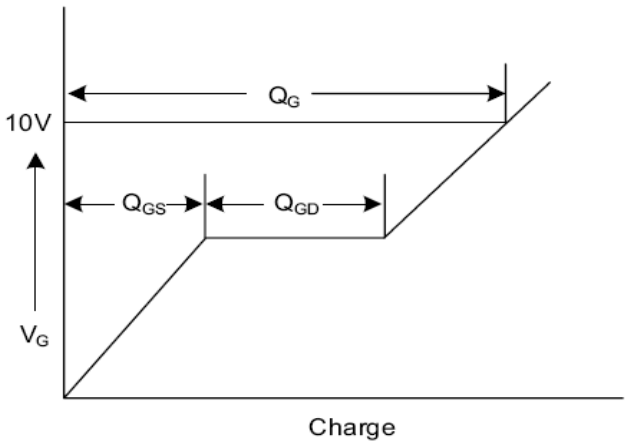


Fig. 3 . 2 Gate Charge Waveform

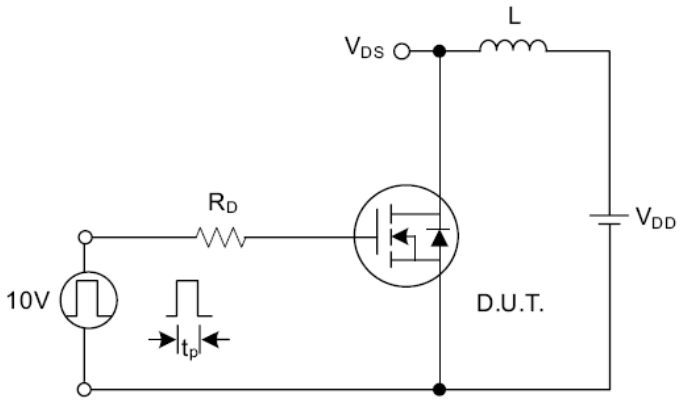


Fig. 4.1 Unclamped Inductive Switching Test Circuit

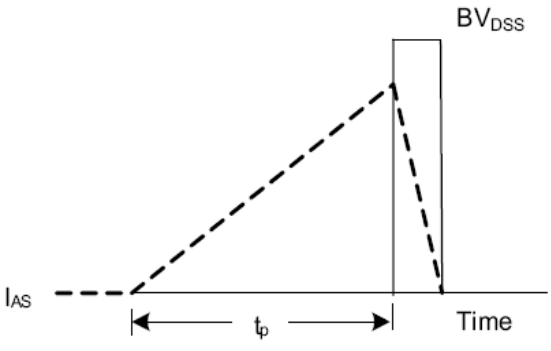


Fig. 4.2 Unclamped Inductive Switching Waveforms

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